

IPA100N08N3GXKSA1

IPA100N08N3GXKSA1 Information



For Reference Only

Part Number IPA100N08N3GXKSA1
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 80V 40A TO220-3

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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IPA100N08N3GXKSA1 Specifications

Manufacturer Part Number IPA100N08N3GXKSA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 40A (Tc) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3.5V @ 46µA Gate Charge (Qg) (Max) @ Vgs 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2410pF @ 40V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 35W (Tc) Rds On (Max) @ Id, Vgs 10 mOhm @ 40A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack		
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Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 40A (Tc) Drive Voltage (Max Rds On, Min Rds On) 6V, 10V Vgs(th) (Max) @ Id 3.5V @ 46µA Gate Charge (Qg) (Max) @ Vgs 35nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2410pF @ 40V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 35W (Tc) Rds On (Max) @ Id, Vgs 10 mOhm @ 40A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)80VCurrent - Continuous Drain (Id) @ 25°C40A (Tc)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.5V @ 46μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2410pF @ 40VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 40A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-FPPackage / CaseTO-220-3 Full Pack	Package	TO-220-3 Full Pack
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 40A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PG-TO220-FP Package / Case MOSFET (Metal Oxide) 80V 80V 80V 40A (Tc) 40A (Tc	Series	OptiMOS?
Drain to Source Voltage (Vdss)80VCurrent - Continuous Drain (Id) @ 25°C40A (Tc)Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.5V @ 46μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2410pF @ 40VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 40A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-FPPackage / CaseTO-220-3 Full Pack	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3.5V @ 46μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 40A, 10V Operating Temperature Supplier Device Package PG-TO220-FP Package / Case 40A (Tc) 6V, 10V 3.5V @ 46μA 3.5V @ 46μA 2410pF @ 40V Though Hole	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)6V, 10VVgs(th) (Max) @ Id3.5V @ 46μAGate Charge (Qg) (Max) @ Vgs35nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2410pF @ 40VVgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 40A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-FPPackage / CaseTO-220-3 Full Pack	Drain to Source Voltage (Vdss)	80V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs In mohm @ 40A, 10V Operating Temperature Supplier Device Package Package / Case South Since (Aux) 3.5V @ 46μA 40V FET Feature - Though Hole Supplier Device Package PG-TO220-FP Package / Case	Current - Continuous Drain (Id) @ 25°C	40A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 40A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	6V, 10V
Input Capacitance (Ciss) (Max) @ Vds 2410pF @ 40V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 40A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack	Vgs(th) (Max) @ Id	3.5V @ 46μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)35W (Tc)Rds On (Max) @ Id, Vgs10 mOhm @ 40A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-FPPackage / CaseTO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	35nC @ 10V
FET Feature - Power Dissipation (Max) 35W (Tc) Rds On (Max) @ Id, Vgs 10 mOhm @ 40A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack	Input Capacitance (Ciss) (Max) @ Vds	2410pF @ 40V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10 mOhm @ 40A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 10 mOhm @ 40A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	35W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	10 mOhm @ 40A, 10V
Supplier Device Package PG-TO220-FP Package / Case TO-220-3 Full Pack	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	PG-TO220-FP
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

IPA100N08N3GXKSA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPA100N08N3GXKSA1 Payment Methods



















IPA100N08N3GXKSA1 Shipping Methods













If you have any question about IPA100N08N3GXKSA1, please do not hesitate to contact us!

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